

isc N-Channel MOSFET Transistor

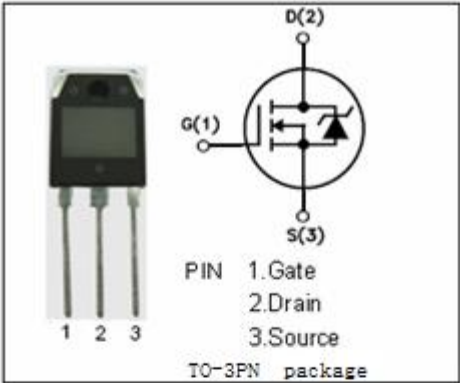
8N55

DESCRIPTION

- Drain Current $I_D = 8A @ T_C = 25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS} = 550V (Min)$
- Fast Switching Speed

APPLICATIONS

- General purpose power amplifier

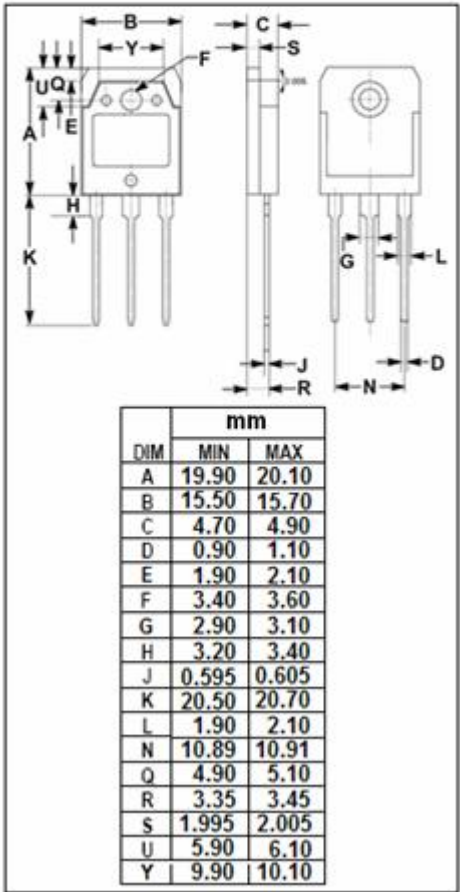


ABSOLUTE MAXIMUM RATINGS($T_C = 25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	550	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C = 25^{\circ}C$	8	A
$I_{D(puls)}$	Pulse Drain Current	32	A
P_{tot}	Total Dissipation@ $T_C = 25^{\circ}C$	75	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.83	$^{\circ}C/W$



isc N-Channel MOSFET Transistor**8N55**• ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=250\mu\text{A}$	550			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D=1\text{mA}$	2.0		4.5	V
V_{SD}	Diode Forward On-Voltage	$I_S=8\text{A}$; $V_{GS}=0$			2.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}$; $I_D=4\text{A}$			1.5	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}$; $V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=550\text{V}$; $V_{GS}=0$			200	μA